



## Description

The PMV48XP uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.



SOT-23

## General Features

$V_{DS} = -20V, I_D = -4.2A$

$R_{DS(ON)} < 55m\Omega @ V_{GS}=-4.5V$

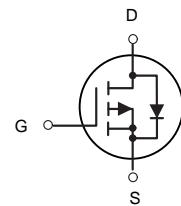
$R_{DS(ON)} < 75m\Omega @ V_{GS}=-2.5V$

## Application

PWM applications

Load switch

Power management



P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
PMV48XP	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current-Continuous	-4.2	A
$I_{DM}$	Drain Current-Pulsed (Note 1)	-15	A
$P_D$	Maximum Power Dissipation	1.7	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient (Note 2)	74	°C/W



**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.45	-0.7	-1.0	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$	-	48	55	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-3\text{A}$	-	60	75	
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-4.2\text{A}$	-	6	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-4\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	740	-	PF
Output Capacitance	$C_{\text{oss}}$		-	290	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	190	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-4\text{V}, R_{\text{L}}=-1.2\Omega, V_{\text{GEN}}=-4.5\text{V}, R_{\text{g}}=1\Omega$	-	12	-	nS
Turn-on Rise Time	$t_{\text{r}}$		-	35	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	30	-	nS
Turn-Off Fall Time	$t_{\text{f}}$		-	10	-	nS
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{DS}}=-4\text{V}, I_{\text{D}}=-4.1\text{A}, V_{\text{GS}}=-4.5\text{V}$	-	7.8	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	1.2	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	1.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=-4.1\text{A}$	-	-	-1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_{\text{s}}$		-	-	-4.1	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production



### Typical Electrical and Thermal Characteristics

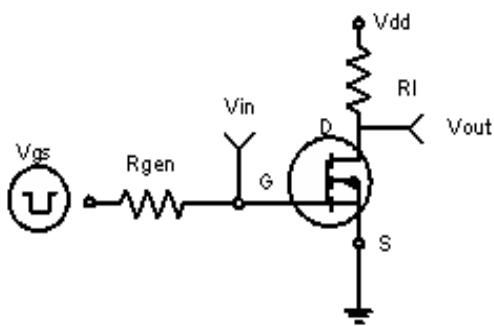


Figure 1:Switching Test Circuit

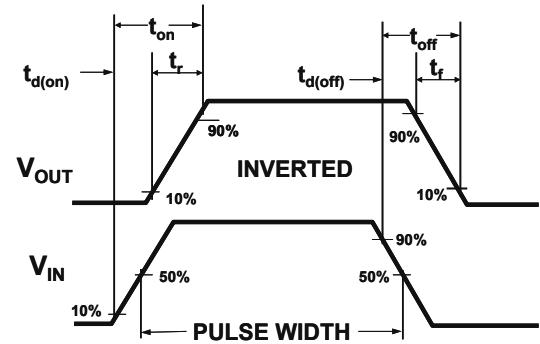
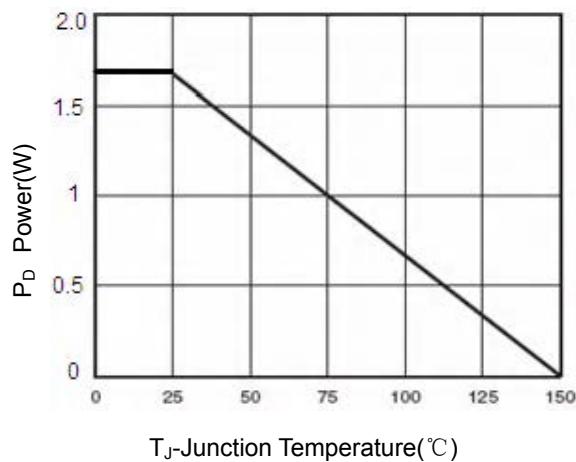
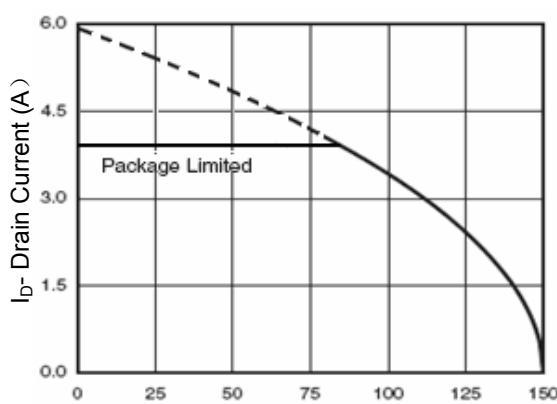


Figure 2:Switching Waveforms



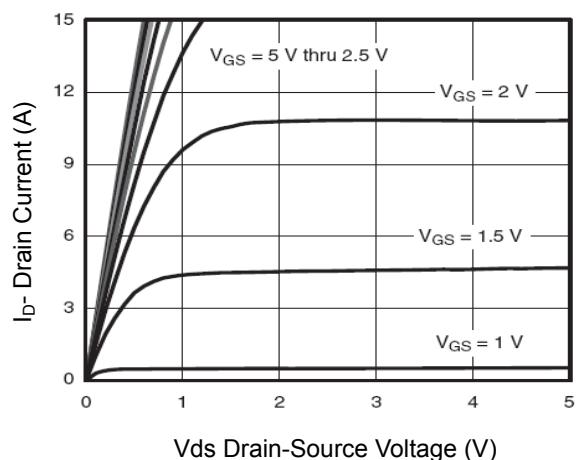
T<sub>J</sub>-Junction Temperature(°C)

Figure 3 Power Dissipation



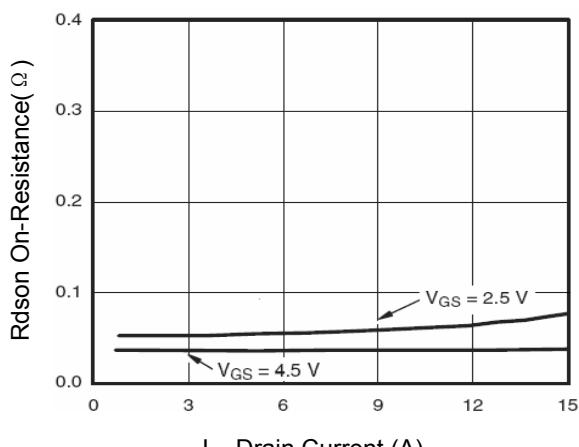
T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Drain Current



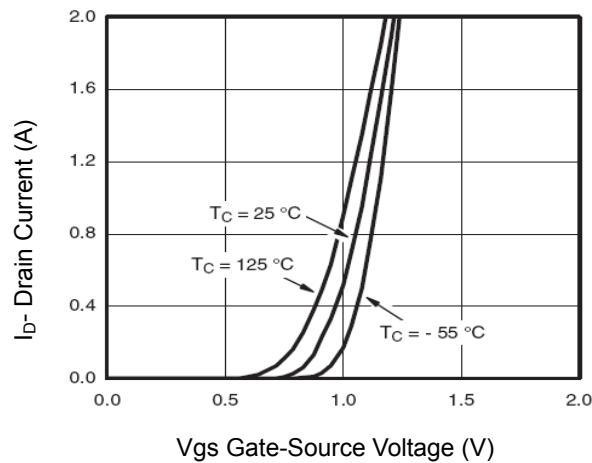
Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics

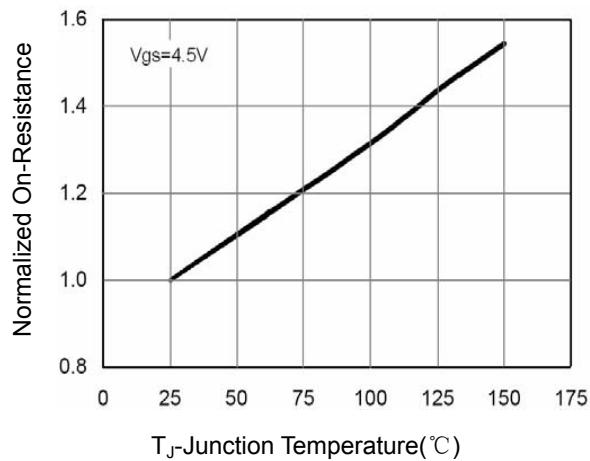


ID- Drain Current (A)

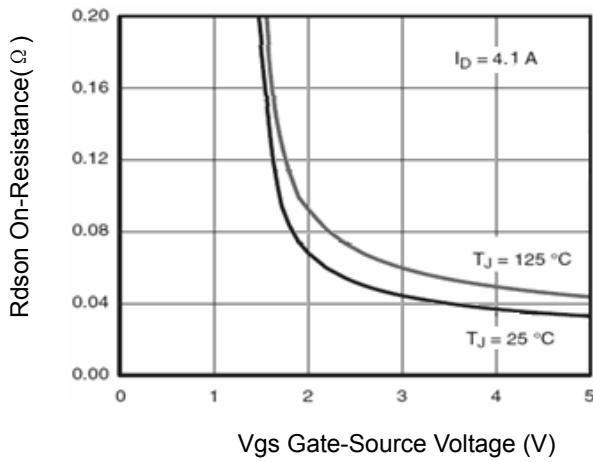
Figure 6 Drain-Source On-Resistance



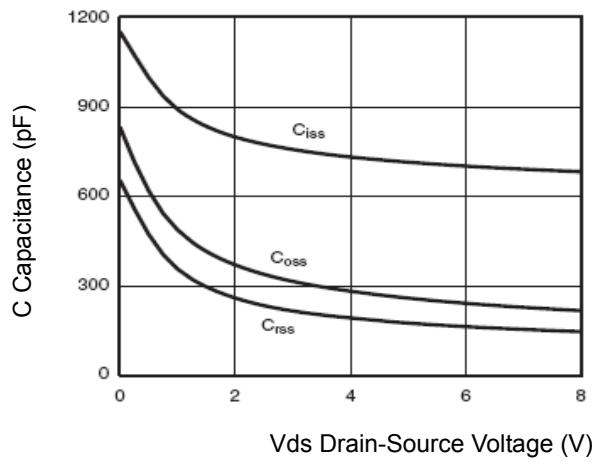
**Figure 7 Transfer Characteristics**



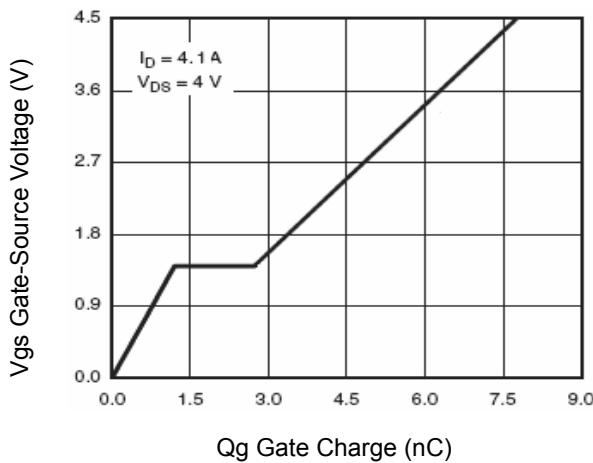
**Figure 8 Drain-Source On-Resistance**



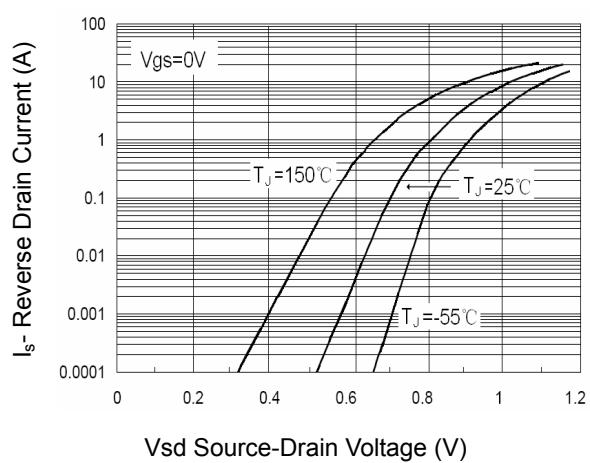
**Figure 9  $R_{DS(on)}$  vs  $V_{GS}$**



**Figure 10 Capacitance vs  $V_{DS}$**



**Figure 11 Gate Charge**



**Figure 12 Source-Drain Diode Forward**

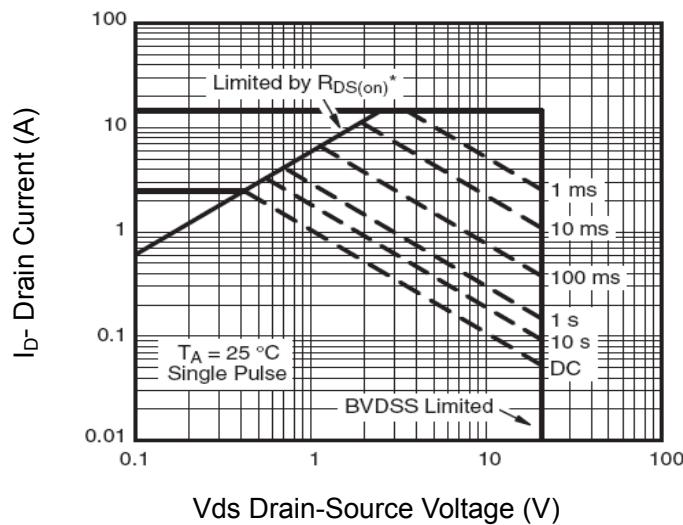


Figure 13 Safe Operation Area

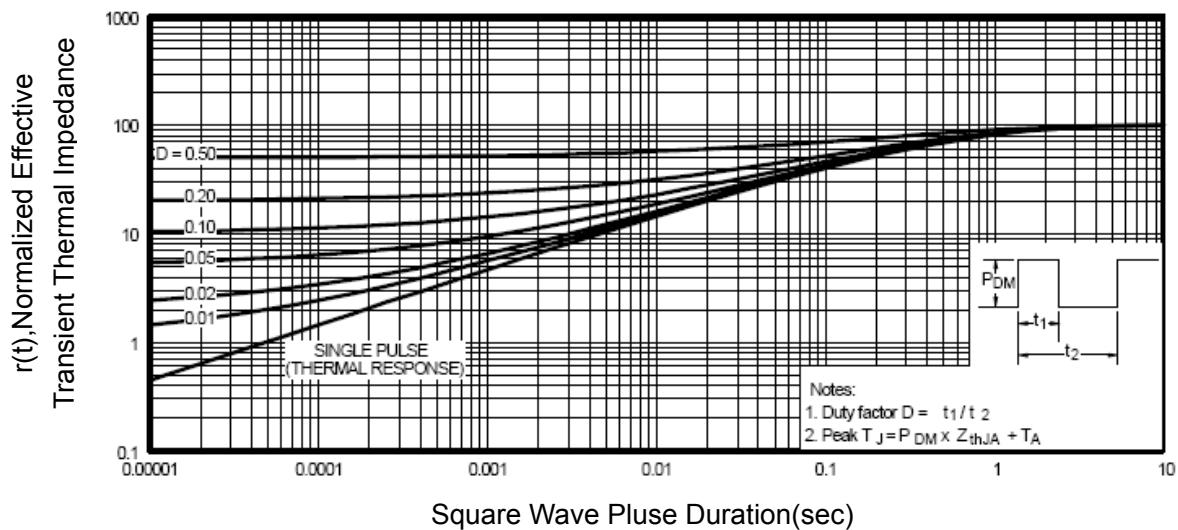
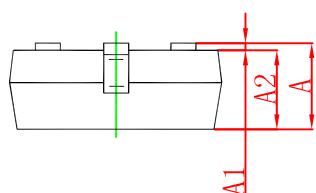
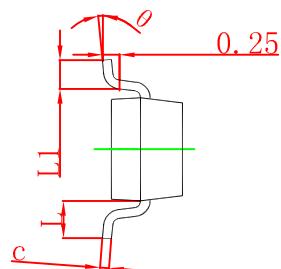
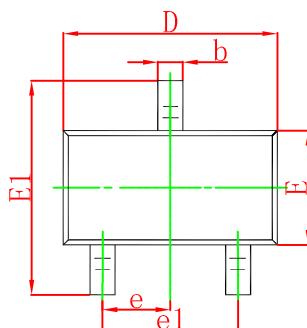


Figure 14 Normalized Maximum Transient Thermal Impedance

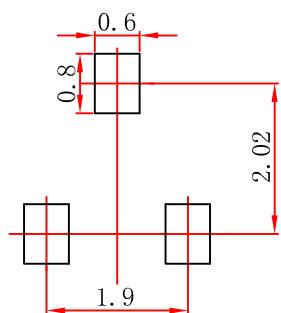


## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.



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